



KI SEMICONDUCTOR CO.

SOT-23 Plastic-Encapsulate Diodes

1SS181

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 150 mW(Tamb=25°C)

Forward Current

I_F : 100 mA

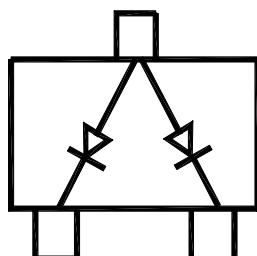
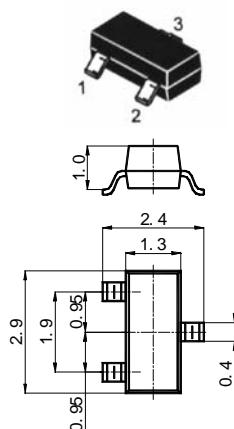
Reverse Voltage

V_R : 80 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

SOT-23



Marking A3

ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R = 80V$		0.5	μA
Forward voltage	V_F	$I_F = 100mA$		1.2	V
Diode capacitance	C_D	$V_R = 0V$ $f = 1MHz$		4	pF
Reverse recovery time	t_{rr}			4	nS